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Siliup Semiconductor

BSS139

60V N-Channel MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	2Ω@10V	0.22A
	2.5Ω@4.5V	

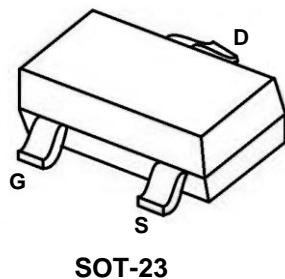
Feature

- We declare that the material of product compliance with RoHS requirements and Halogen Free
- Low threshold voltage,makes it ideal for low voltage applications
- ESD Protected

Application

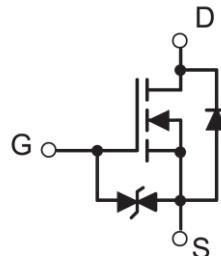
- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays

Package

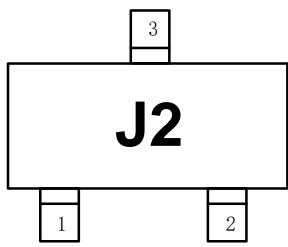


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Circuit diagram



Marking



J2 =Device Code



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Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _D	0.22	A
Power Dissipation	P _D	0.35	W
Thermal Resistance from Junction to Ambient	R _{θJA}	357	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C

Electrical characteristics (T_A=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	60			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = 48V, V _{GS} = 0V			1	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±5	μA
Gate threshold voltage ¹⁾	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	0.7	1	1.45	V
Drain-source on-resistance ¹⁾	R _{DS(on)}	V _{GS} = 10V, I _D = 500mA		2	5	Ω
		V _{GS} = 4.5V, I _D = 200mA		2.5	8	
Dynamic characteristics²⁾						
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1MHz		27		pF
Output Capacitance	C _{oss}			13		
Reverse Transfer Capacitance	C _{rss}			6		
Switching Characteristics¹⁾²⁾						
Turn-on delay time	t _{d(on)}	V _{DD} =30V, I _D =0.29A, V _{GS} =10V, R _G =6Ω			5	nS
Rise time	t _r				18	
Turn-off delay time	t _{d(off)}				36	
Fall time	t _f				14	
Source-Drain Diode characteristics						
Diode Forward voltage	V _{SD}	V _{GS} = 0V, I _s = 500mA	0.5		1.4	V

Notes:

- 1) Pulse Test: Pulse Width ≤300μs, Duty Cycle ≤2%.



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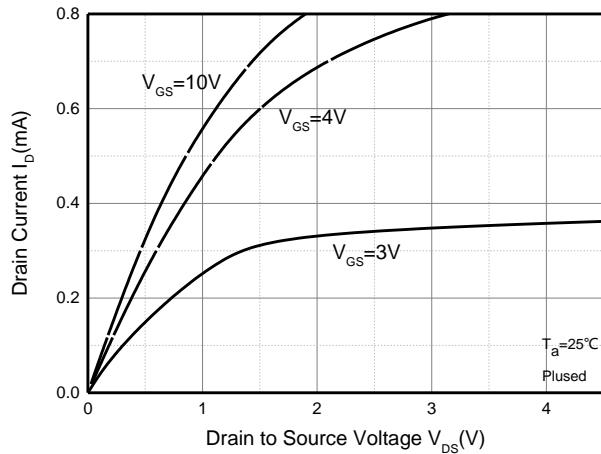
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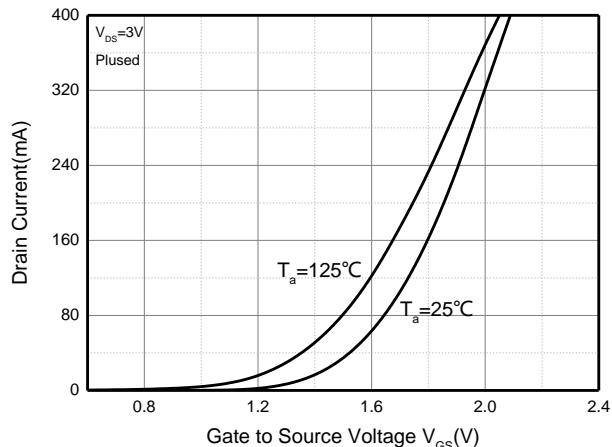
60V N-Channel MOSFET

Typical Characteristics

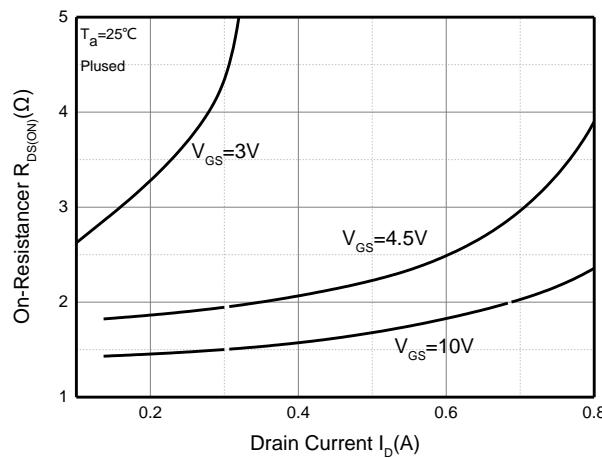
Output Characteristics



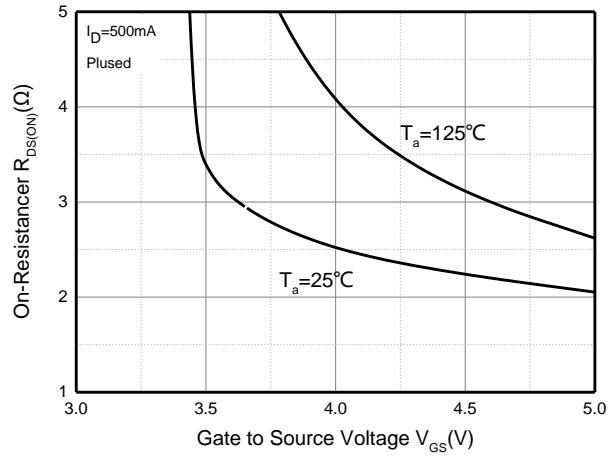
Transfer Characteristics



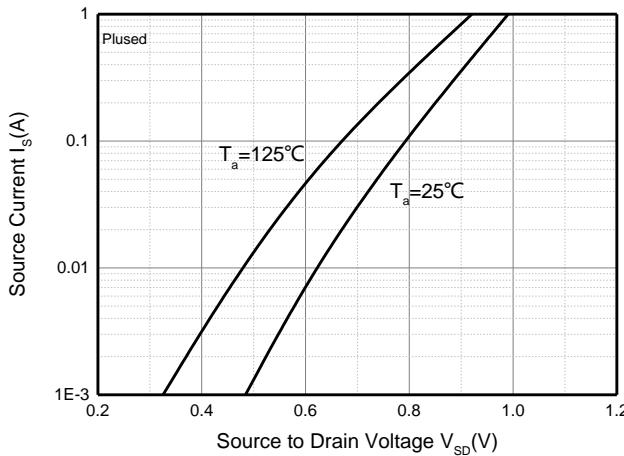
RDS(ON) — ID



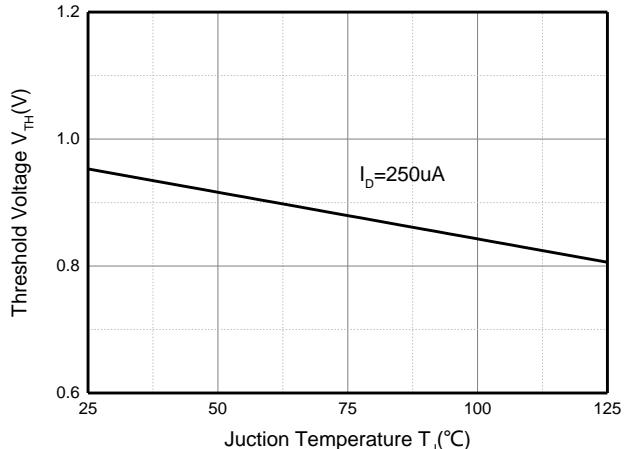
RDS(ON) — VGS



IS — VSD



Threshold Voltage





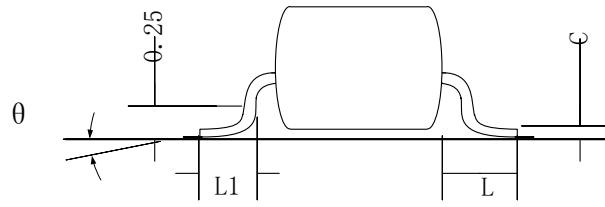
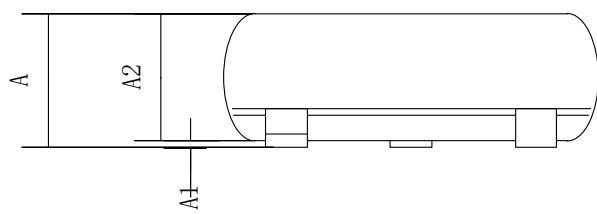
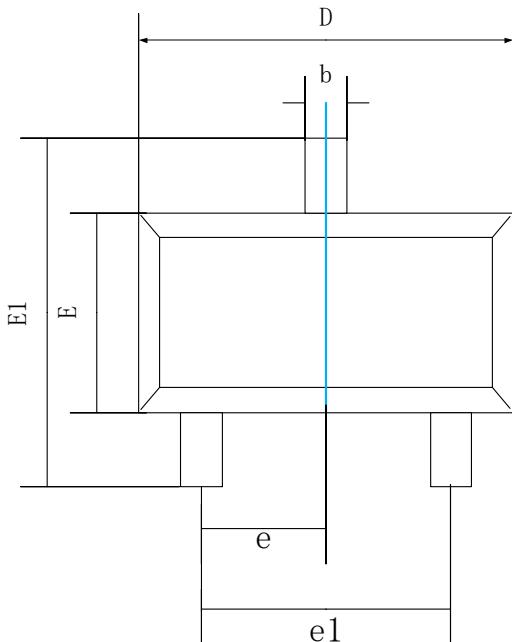
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SOT-23 Package Information



共面度0-0.09mm

Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50
θ	0°	8°